

FUJIOKA et al.

Serial No.: 10/098,631

Amendment dated December 9, 2003

Response to Office Action dated September 11, 2003

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application. By the present amendment, claim 1 has been amended, non-elected claims 3-11 have been canceled and new claims 12-15 have been added.

Listing of Claims:

Claim 1. (*Currently Amended*) A point emission type light emitting element comprising:

a stripe ridge having an n-type layer, an active layer and a p-type layer that are formed from semiconductors on a substrate, so as to emit light from one end face of the stripe ridge,

wherein the stripe ridge has a protruding portion on the end face and the surface of the light emitting element is covered with ~~an~~ a shading film except for the tip of the protruding portion, and

wherein a step portion is formed between the stripe ridge and the protruding portion.

Claim 2. (*Currently Amended*) The point emission type light emitting element according to claim 1[[;]], wherein said n-type layer, said active layer and said p-type layer ~~are made of~~ comprise nitride semiconductor.

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Claims 3-11. (*Canceled*)

Claim 12. (*New*) The point emission type light emitting element according to claim 1, wherein the width of the stripe ridge is in a range from 1 μ m to 100 μ m.

Claim 13. (*New*) The point emission type light emitting element according to claim 1, wherein the width of the protruding portion is in a range from 1 μ m to 10 μ m.

Claim 14. (*New*) The point emission type light emitting element according to claim 1, wherein the shading film comprises a material selected from the group consisting of Cr/Ni, TiO₂, SiO₂, Cr, Ti/Pt, Ti, Ni, Al, Ag and Au.

Claim 15. (*New*) The point emission type light emitting element according to claim 1, wherein the ridge stripe is formed by etching to a depth that does not reach the active layer and the protruding portion is formed by etching to a depth that reaches the n-type layer.